National Semiconductor

February 1986

DS3245 Quad MOS Clock Driver

General Description

The DS3245 is a quad bipolar-to-MOS clock driver with TTL compatible inputs. It is designed to provide high output current and voltage capabilities necessary for optimum driving of high capacitance N-channel MOS memory systems.

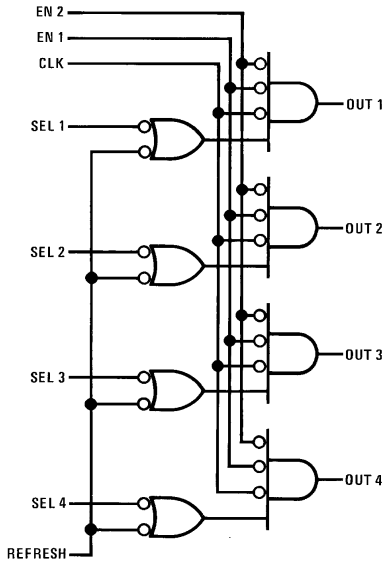
Only 2 supplies, 5 V_{DC} and 12 V_{DC}, are required without compromising the usual high V_{OH} specification obtained by circuits using a third supply.

The device features 2 common enable inputs, a refresh input, and a clock control input for simplified system designs. The circuit was designed for driving highly capacitive loads at high speeds and uses Schottky-clamped transistors. PNP transistors are used on all inputs, thereby minimizing input loading.

Features

- TTL compatible inputs
- Operates from 2 standard supplies: 5 V_{DC}, 12 V_{DC}
- Internal bootstrap circuit eliminates need for external PNP's
- PNP inputs minimize loading
- High voltage/current outputs
- Input and output clamping diodes
- Control logic optimized for use with MOS memory systems
- Pin and function equivalent to Intel 3245

Logic and Connection Diagrams



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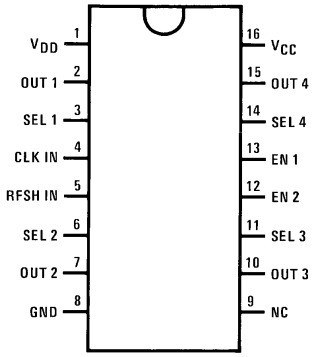
Dual-In-Line Package



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Top View

Order Number DS3245J or DS3245N
See NS Package Number J16A or N16A

RRD-B30M115/Printed in U. S. A.

Absolute Maximum Ratings

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Temperature Under Bias	−10°C to +85°C
Storage Temperature	−65°C to +150°C
Supply Voltage, V_{CC}	−0.5V to +7V
Supply Voltage, V_{DD}	−0.5V to +14V
All Input Voltages	−1.0V to V_{DD}
Outputs for Clock Driver	−1.0V to V_{DD} + 1V
Maximum Power Dissipation* at 25°C	
Cavity Package	1509 mW
Molded Package	1476 mW

*Derate cavity package 10.1 mW/°C above 25°C; derate molded package 11.8 mW/°C above 25°C.

Operating Conditions

	Min	Max	Units
Supply Voltage, V_{CC}	4.75	5.25	V
Supply Voltage, V_{DD}	11.4	12.6	V
Operating Temperature $9T_A$	0	75	°C

Electrical Characteristics (Notes 2 and 3)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
I_{FD}	Select Input Load Current	V_F = 0.45V			−0.25	mA
I_{FE}	Enable Input Load Current	V_F = 0.45V			−1.0	mA
I_{RD}	Select Input Leakage Current	V_R = 5V			10	μA
I_{RE}	Enable Input Leakage Current	V_R = 5V			40	μA
V_{OL}	Output Low Voltage	I_{OL} = 5 mA, V_{IH} = 2V			0.45	V
		I_{OL} = −5 mA	−1.0			V
V_{OH}	Output High Voltage	I_{OH} = −1 mA, V_{IL} = 0.8V	V_{DD} − 0.50			V
		I_{OH} = 5 mA			V_{DD} + 1.0	V
V_{IL}	Input Low Voltage, All Inputs				0.8	V
V_{IH}	Input High Voltage, All Inputs		2			V
V_{CLAMP}	Input Clamp Voltage	V_{CC} = Min, I_{IN} = −12 mA		−1.0	−1.5	V

Power Supply Current Drain

Symbol	Parameter	Conditions	Min	Typ	Max	Units
I_{CC}	Current from V_{CC} Output in High State	V_{CC} = 5.25V, V_{DD} = 12.6V		26	34	mA
I_{DD}	Current from V_{DD} Output in High State	V_{CC} = 5.25V, V_{DD} = 12.6V		23	30	mA
I_{CC}	Current from V_{CC} Output in Low State	V_{CC} = 5.25V, V_{DD} = 12.6V		29	39	mA
I_{DD}	Current from V_{DD} Output in Low State	V_{CC} = 5.25V, V_{DD} = 12.6V		13	19	mA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the 0°C to +°C range. All typical values are for T_A = 25°C and V_{CC} = 5V and V_{DD} = 12V.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Switching Characteristics $T_A = 0°C$ to $+75°C$, $V_{CC} = 5V \pm 5\%$, $V_{DD} = 12V \pm 5\%$

Symbol	Parameter	Conditions	Min(1)	Typ(2,4)	Max(3)	Units
t_{-+}	Input to Output Delay	$R_{SERIES} = 0$	5	11		ns
t_{DR}	Delay Plus Rise Time	$R_{SERIES} = 0$		20	32	ns
t_{+-}	Input to Output Delay	$R_{SERIES} = 0$	3	7		ns
t_{DF}	Delay Plus Fall Time	$R_{SERIES} = 0$		18	32	ns
t_T	Output Transition Time	$R_{SERIES} = 20\Omega$	10	17	25	ns
t_{DR}	Delay Plus Rise Time	$R_{SERIES} = 20\Omega$		27	38	ns
t_{DF}	Delay Plus Fall Time	$R_{SERIES} = 20\Omega$		25	38	ns

Capacitance $T_A = 25°C$(5)

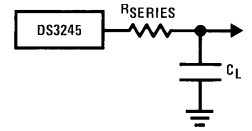
Symbol	Parameter	Conditions	Min	Typ	Max	Units
C_{IN}	Input Capacitance, $\overline{I}_1$, $\overline{I}_2$, $\overline{I}_3$, $\overline{I}_4$			5	8	pF
C_{IN}	Input Capacitance, $\overline{R}$, $\overline{C}$, $\overline{E}1$, $\overline{E}2$			8	12	pF

Note 1: $C_L = 150$ pF
Note 2: $C_L = 200$ pF
Note 3: $C_L = 250$ pF
} These values represent a range of total stray plus clock capacitance for nine 4k RAMs.

Note 4: Typical values are measured at 25°C.

Note 5: This parameter is periodically sampled and is not 100% tested. Condition of measurement is f = 1 MHz, $V_{BIAS} = 2V$, $V_{CC} = 0V$, and $T_A = 25°C$.

AC Test Circuit and Switching Time Waveforms



Input pulse amplitudes: 3V
Input pulse rise and fall times:
5 ns between 1V and 2V
Measurements points: see waveforms

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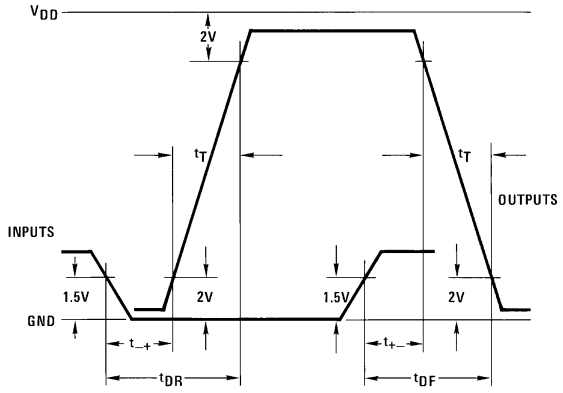

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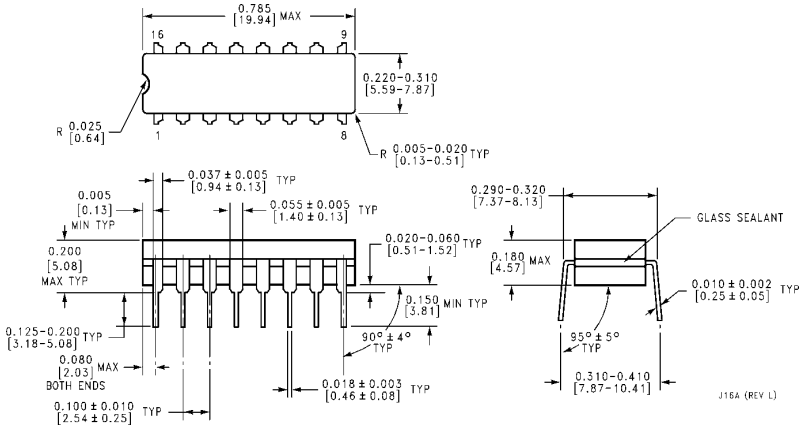
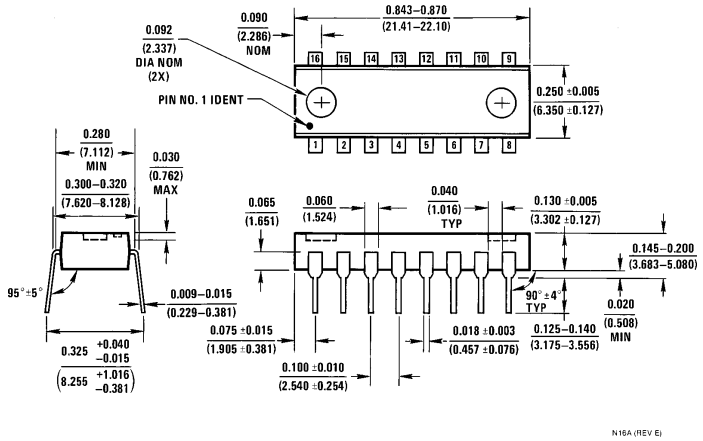
Physical Dimensions inches (millimeters)



Ceramic Dual-in-Line Package (J)
Order Number DS3245J
NS Package Number J16A



Molded Dual-in-Line Package (N)
Order Number DS3245N
NS Package Number N16A

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National Semiconductor Corporation
1111 West Bardin Road
Arlington, TX 76017
Tel: 1(800) 272-9959
Fax: 1(800) 737-7018

National Semiconductor Europe
Fax: (+49) 0-180-530 85 86
Email: cnjwge@tevm2.nsc.com
Deutsch Tel: (+49) 0-180-530 85 85
English Tel: (+49) 0-180-532 78 32
Français Tel: (+49) 0-180-532 93 58
Italiano Tel: (+49) 0-180-534 16 80

National Semiconductor Hong Kong Ltd.
13th Floor, Straight Block,
Ocean Centre, 5 Canton Rd.
Tsimshatsui, Kowloon
Hong Kong
Tel: (852) 2737-1600
Fax: (852) 2736-9960

National Semiconductor Japan Ltd.
Tel: 81-043-299-2309
Fax: 81-043-299-2408